Chun-Hu Cheng

List of Publications by Year
in descending order

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158	2,054	279798	302126
papers	citations	23 h-index	39 g-index

159	159	159	2177
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Effect of capping layer on the ferroelectricity of hafnium oxide. Thin Solid Films, 2022, 753, 139274.	1.8	3
2	Performance investigation of hafnium-oxide negative capacitance transistor with remote nitrogen plasma treatment. Thin Solid Films, 2022, 755, 139345.	1.8	0
3	Electrical Characteristics Investigation of Ferroelectric Memories Using Stacked and Mixed Hafnium Zirconium Oxides. Thin Solid Films, 2022, , 139395.	1.8	1
4	Impact of stress and doping effects on the polarization behavior and electrical characteristics of hafniumâ€“zirconium oxides. Ceramics International, 2021, 47, 2864-2868.	4.8	4
5	Effect of plasma oxidation on tin-oxide active layer for thin-film transistor applications. Journal of Materials Science, 2021, 56, 6286-6291.	3.7	6
6	Development of Optimum Preparation Conditions of Fe-Deficient M-Type Caâ€“Srâ€“La System Hexagonal Ferrite Magnet. IEEE Transactions on Magnetics, 2021, 57, 1-7.	2.1	5
7	Simultaneous Analysis of Multi-Variables Effect on the Performance of Multi-Domain MFIS Negative Capacitance Field-Effect Transistors. IEEE Journal of the Electron Devices Society, 2021, 9, 741-747.	2.1	5
8	High performance negative capacitance field-effect transistor featuring low off-state current, high on/off current ratio, and steep sub-60 mV dec^{â^'1} swing. Japanese Journal of Applied Physics, 2020, 59, SGGA01.	1.5	3
9	Characteristic Simulation of Hybrid Multilayer Junctionless Field Effect Transistors with Negative Capacitance Effect. IEEE Nanotechnology Magazine, 2020, 19, 89-93.	2.0	4
10	Preparation and magnetic properties of high performance Caâ€“Sr based M-type hexagonal ferrites. Results in Materials, 2020, 8, 100150.	1.8	3
11	Impact of Series-Connected Ferroelectric Capacitor in HfOâ‚‚-Based Ferroelectric Field-Effect Transistors for Memory Application. IEEE Journal of the Electron Devices Society, 2020, 8, 1076-1081.	2.1	3
12	Physical Modeling of p-Type Fluorinated Al-Doped Tin-Oxide Thin Film Transistors. IEEE Journal of the Electron Devices Society, 2020, 8, 948-958.	2.1	10
13	A pâ€Type Ferroelectric Fieldâ€Effect Transistor Using Ultrathin Hafnium Aluminum Oxide. Physica Status Solidi - Rapid Research Letters, 2020, 14, 2000356.	2.4	3
14	A comparative study of metal-ferroelectric-metal devices using doped- and stacked-hafnium zirconium oxides. Thin Solid Films, 2020, 701, 137927.	1.8	3
15	Negative Capacitance CMOS Field-Effect Transistors with Non-Hysteretic Steep Sub-60mV/dec Swing and Defect-Passivated Multidomain Switching. , 2019, , .		7
16	Gammaâ€Ray Irradiation Effect on Ferroelectric Devices with Hafnium Aluminum Oxides. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900414.	2.4	0
17	Stabilizing Ferroelectric Domain Switching of Hafnium Aluminum Oxide Using Metal Nitride Electrode Engineering. ECS Journal of Solid State Science and Technology, 2019, 8, P553-P556.	1.8	3
18	Investigation on polarization characteristics of ferroelectric memories with thermally stable hafnium aluminum oxides. Vacuum, 2019, 166, 11-14.	3.5	13

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19	Effect of Plasma Fluorination in p-Type SnO TFTs: Experiments, Modeling, and Simulation. IEEE Transactions on Electron Devices, 2019, 66, 1314-1321.	3.0	31
20	Investigation of Phase Transformation in HfO2 Ferroelectric Capacitor by Means of a ZrO2 Capping Layer. , 2019, , .		4
21	Ferroelectric Characterization of Hafnium-Oxide-Based Ferroelectric Memories with Remote Nitrogen Plasma Treatments. , 2019, , .		0
22	Forming-Free SiGeOx/TiOy Resistive Random Access Memories Featuring Large Current Distribution Windows. Journal of Nanoscience and Nanotechnology, 2019, 19, 7916-7919.	0.9	4
23	Progress and challenges in p-type oxide-based thin film transistors. Nanotechnology Reviews, 2019, 8, 422-443.	5.8	42
24	Simulation of Poly-Silicon Thin Film Transistors with Negative Capacitance Effect. , 2019, , .		0
25	Impact of Zirconium Doping on Steep Subthreshold Switching of Negative Capacitance Hafnium Oxide Based Transistors. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1800573.	2.4	8
26	Implementation of Dopant-Free Hafnium Oxide Negative Capacitance Field-Effect Transistor. IEEE Transactions on Electron Devices, 2019, 66, 825-828.	3.0	25
27	Investigation of Gate-Stress Engineering in Negative Capacitance FETs Using Ferroelectric Hafnium Aluminum Oxides. IEEE Transactions on Electron Devices, 2019, 66, 1082-1086.	3.0	17
28	Improved Negativeâ€Capacitance Switch of Ferroelectric Field Effect Transistor Using Defect Passivation Engineering. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1800493.	2.4	4
29	Editorial: IEDMS 2016. Microelectronics Reliability, 2018, 83, 207.	1.7	0
30	Interface engineering of ferroelectric negative capacitance FET for hysteresis-free switch and reliability improvement. , 2018, , .		6
31	Effect of specific surface area of raw material Fe2O3 on magnetic properties of YIG. Journal of Magnetism and Magnetic Materials, 2018, 449, 157-164.	2.3	8
32	Influence of CaCO3 and SiO2 additives on magnetic properties of M-type Sr ferrites. Journal of Magnetism and Magnetic Materials, 2018, 451, 288-294.	2.3	24
33	Direct Fabrication of Inkjet-Printed Dielectric Film for Metalâ€“Insulatorâ€“Metal Capacitors. Journal of Electronic Materials, 2018, 47, 677-683.	2.2	4
34	Investigation of Polarization Hysteresis and Transient Current Switching in Ferroelectric Aluminum-Doped Hafnium Oxides. , 2018, , .		3
35	Achieving High-Scalability Negative Capacitance FETs with Uniform Sub-35 mV/dec Switch Using Dopant-Free Hafnium Oxide and Gate Strain. , 2018, , .		7
36	Improved Thermal Stability and Stress Immunity in Highly Scalable Junctionless FETs Using Enhanced-Depletion Channels. ECS Journal of Solid State Science and Technology, 2018, 7, Q242-Q245.	1.8	3

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37	On the Electrical Characteristics of Ferroelectric FinFET Using Hafnium Zirconium Oxide with Optimized Gate Stack. ECS Journal of Solid State Science and Technology, 2018, 7, P640-P646.	1.8	3
38	Paraelectric-Ferroelectric Transition in Hafnium-Oxide-Based Ferroelectric Memory. , 2018, , .		2
39	Performance Enhancements in p-Type Al-Doped Tin-Oxide Thin Film Transistors by Using Fluorine Plasma Treatment. IEEE Electron Device Letters, 2017, 38, 210-212.	3.9	26
40	Investigation of strain-induced phase transformation in ferroelectric transistor using metal-nitride gate electrode. Physica Status Solidi - Rapid Research Letters, 2017, 11, 1600368.	2.4	27
41	Investigation of Electrical Characteristics on 25-nm InGaAs Channel FinFET Using InAlAs Back Barrier and Al₂O₃Gate Dielectric. ECS Journal of Solid State Science and Technology, 2017, 6, Q58-Q62.	1.8	2
42	Influence of plasma fluorination on p -type channel tin-oxide thin film transistors. Journal of Alloys and Compounds, 2017, 707, 162-166.	5.5	39
43	Magnetic property enhancement of cobalt-free M-type strontium hexagonal ferrites by CaCO 3 and SiO 2 addition. Intermetallics, 2017, 89, 111-117.	3.9	16
44	A high output power and low phase noise GaN HEMT VCO with array of switchable inductors. International Journal of Circuit Theory and Applications, 2017, 45, 1621-1636.	2.0	1
45	Channel Modification Engineering by Plasma Processing in Tin-Oxide Thin Film Transistor: Experimental Results and First-Principles Calculation. ECS Journal of Solid State Science and Technology, 2017, 6, Q53-Q57.	1.8	4
46	The new FCL with HTS for the high-speed communication system. Microwave and Optical Technology Letters, 2017, 59, 964-966.	1.4	0
47	Experimental Observation of Negative Capacitance Switching Behavior in Oneâ€Transistor Ferroelectric Versatile Memory. Physica Status Solidi - Rapid Research Letters, 2017, 11, 1700098.	2.4	21
48	Using nanoindentation to investigate the temperature cycling of Sn 37Pb solders. Microelectronics Reliability, 2017, 78, 111-117.	1.7	2
49	Effect of body bias and temperature on low-frequency noise in 40-nm nMOSFETs. Microelectronics Reliability, 2017, 78, 267-271.	1.7	4
50	Fast Low-Temperature Plasma Process for the Application of Flexible Tin-Oxide-Channel Thin Film Transistors. IEEE Nanotechnology Magazine, 2017, 16, 876-879.	2.0	18
51	Impact of ferroelectric domain switching in nonvolatile charge-trapping memory. , 2017, , .		2
52	Energy-Efficient Versatile Memories With Ferroelectric Negative Capacitance by Gate-Strain Enhancement. IEEE Transactions on Electron Devices, 2017, 64, 3498-3501.	3.0	26
53	Improved electrical characteristics and reliability of multi-stacking PNPN junctionless transistors using channel depletion effect. , 2017, , .		0
54	High speed negative capacitance ferroelectric memory. , 2017, , .		0

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55	Investigation of Double-Snapback Characteristic in Resistor-Triggered SCRs Stacking Structure. IEEE Transactions on Electron Devices, 2017, 64, 4200-4205.	3.0	16
56	Energy-efficient HfAlO<inf>x</inf> NCFET: Using gate strain and defect passivation to realize nearly hysteresis-free sub-25mV/dec switch with ultralow leakage. , 2017, , .		17
57	Program/erase speed and data retention trade-off in negative capacitance versatile memory. , 2017, , .		1
58	Photocapacitive effect of ferroelectric hafnium-zirconate capacitor structure. , 2017, , .		0
59	Ultrasonic dissimilar joining of aluminum alloy and polymer with the composite material of ABS polymer doping carbonized rice husk. MATEC Web of Conferences, 2017, 130, 06001.	0.2	3
60	High holding voltage segmentation stacking silicon-controlled-rectifier structure with field implant as body ties blocking layer. Japanese Journal of Applied Physics, 2016, 55, 04ER10.	1.5	1
61	Bipolar Conduction in Tin-Oxide Semiconductor Channel Treated by Oxygen Plasma for Low-Power Thin-Film Transistor Application. Journal of Display Technology, 2016, 12, 224-227.	1.2	14
62	One-transistor ferroelectric versatile memory: Strained-gate engineering for realizing energy-efficient switching and fast negative-capacitance operation. , 2016, , .		5
63	On the variability of threshold voltage window in gate-injection versatile memories with Sub-60mV/dec subthreshold swing and 1012-cycling endurance. , 2016, , .		0
64	A highly scalable poly-Si junctionless FETs featuring a novel multi-stacking hybrid P/N layer and vertical gate with very high Ion/Ioff for 3D stacked ICs. , 2016, , .		8
65	Pâ€type tinâ€oxide thin film transistors for blueâ€light detection application. Physica Status Solidi - Rapid Research Letters, 2016, 10, 919-923.	2.4	8
66	Gettering Effect Induced by Oxygen-Deficient Titanium Oxide in InZnO and InGaZnO Channel Systems for Low-Power Display Applications. Journal of Display Technology, 2016, 12, 219-223.	1.2	7
67	Impact of nanoscale polarization relaxation on endurance reliability of one-transistor hybrid memory using combined storage mechanisms. , 2015, , .		3
68	The Role of Oxygen Vacancies on Switching Characteristics of TiO_{<I>x</I>} Resistive Memories. Journal of Nanoscience and Nanotechnology, 2015, 15, 4431-4434.	0.9	2
69	TiO₂-Based Indium Phosphide Metal-Oxide-Semiconductor Capacitor with High Capacitance Density. Journal of Nanoscience and Nanotechnology, 2015, 15, 2810-2813.	0.9	2
70	Correlation of thermal annealing effect, crystallinity and electrical characteristics in c-axis crystallized InGaZnO thin-film transistors. Journal of Alloys and Compounds, 2015, 643, S187-S192.	5.5	5
71	Amorphous Titanium Oxide Semiconductors on Quasi-Crystal-Like InGaZnO Channels for Thin Film Transistor Applications. Journal of Display Technology, 2015, 11, 506-511.	1.2	1
72	Investigation of mechanical bending instability in flexible low-temperature-processed electrochromic display devices. Thin Solid Films, 2015, 584, 94-97.	1.8	8

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73	Charge transport in amorphous Hf0.5Zr0.5O2. Applied Physics Letters, 2015, 106, .	3.3	29
74	Nanoscale potential fluctuation in non-stoichiometric HfOx and low resistive transport in RRAM. Microelectronic Engineering, 2015, 147, 165-167.	2.4	20
75	Improvement of dielectric flexibility and electrical properties of mechanically flexible thin film devices using titanium oxide materials fabricated at a very low temperature of 100Â°C. Journal of Alloys and Compounds, 2015, 643, S133-S136.	5.5	13
76	Temperature-Dependent Transfer Characteristics of Low Turn-On Voltage InGaZnO Metal-Oxide Devices With Thin Titanium Oxide Capping Layers. Journal of Display Technology, 2015, 11, 512-517.	1.2	3
77	Structural and electrical characteristics of thin film transistor employing an oriented crystalline InGaZnO channel. Japanese Journal of Applied Physics, 2015, 54, 04DF05.	1.5	2
78	Low power 1T DRAM/NVM versatile memory featuring steep sub-60-mV/decade operation, fast 20-ns speed, and robust 85°C-extrapolated 10¹⁶ endurance. , 2015, , .		14
79	Interface polarization fluctuation effect of ferroelectric hafnium-zirconium-oxide ferroelectric memory with nearly ideal subthreshold slope. , 2015, , .		1
80	Low-Voltage InGaZnO Thin Film Transistors with Small Sub-Threshold Swing. Journal of Nanoscience and Nanotechnology, 2015, 15, 1486-1489.	0.9	7
81	Percolation conductivity in hafnium sub-oxides. Applied Physics Letters, 2014, 105, 262903.	3.3	15
82	High Mobility Bilayer Metalâ€“Oxide Thin Film Transistors Using Titanium-Doped InGaZnO. IEEE Electron Device Letters, 2014, 35, 87-89.	3.9	56
83	Performance comparison of titanium-oxide resistive switching memories using GeO_x and AlO_x capping layers for flexible application. Japanese Journal of Applied Physics, 2014, 53, 061502.	1.5	1
84	High Mobility Field-Effect Thin Film Transistor Using Room-Temperature High-<formula formulatype="inline"><tex Notation="TeX">$kappa$</tex> </formula> Gate Dielectrics. Journal of Display Technology, 2014, 10, 875-881.	1.2	10
85	Improved highâ€temperature switching characteristics of Y₂O₃/TiO_x resistive memory through carrier depletion effect. Physica Status Solidi - Rapid Research Letters, 2014, 8, 431-435.	2.4	8
86	Nanotribological properties of ALD-processed bilayer TiO2/ZnO films. Microelectronics Reliability, 2014, 54, 2754-2759.	1.7	10
87	Origin of traps and charge transport mechanism in hafnia. Applied Physics Letters, 2014, 105, 222901.	3.3	38
88	Nanotribological behavior of ZnO films prepared by atomic layer deposition. Journal of Physics and Chemistry of Solids, 2014, 75, 334-338.	4.0	5
89	Sub-micro watt resistive memories using nano-crystallized aluminum oxynitride dielectric. Applied Physics A: Materials Science and Processing, 2014, 116, 575-579.	2.3	4
90	Low-Leakage-Current DRAM-Like Memory Using a One-Transistor Ferroelectric MOSFET With a Hf-Based Gate Dielectric. IEEE Electron Device Letters, 2014, 35, 138-140.	3.9	110

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91	Structural stability of diffusion barriers in thermoelectric SbTe: From first-principles calculations to experimental results. Journal of Alloys and Compounds, 2014, 588, 633-637.	5.5	9
92	An Oxygen Gettering Scheme for Improving Device Mobility and Subthreshold Swing of InGaZnO-Based Thin-Film Transistor. IEEE Nanotechnology Magazine, 2014, 13, 933-938.	2.0	14
93	Amorphous bilayer TiO2â€“InGaZnO thin film transistors with low drive voltage. Solid-State Electronics, 2014, 99, 51-54.	1.4	12
94	Low-Voltage Steep Turn-On pMOSFET Using Ferroelectric High-$kappa$ Gate Dielectric. IEEE Electron Device Letters, 2014, 35, 274-276.	3.9	112
95	Performance improvement of electrochromic display devices employing micro-size precipitates of tungsten oxide. Applied Physics A: Materials Science and Processing, 2014, 116, 1553-1559.	2.3	5
96	Low power resistive random access memory using interface-engineered dielectric stack of SiOx/a-Si/TiOy with 1D1R-like structure. Current Applied Physics, 2014, 14, 139-143.	2.4	10
97	Operation mechanism investigation of electrochromic display devices using tungsten oxides based on solid-state metalâ€“oxideâ€“metal capacitor structures. Solid-State Electronics, 2014, 99, 16-20.	1.4	4
98	Interfaceâ€engineered resistive memory using plasmaâ€modified electrode on polyimide substrate. Physica Status Solidi - Rapid Research Letters, 2014, 8, 100-104.	2.4	2
99	Schottky-Barrier Resistive Memory with Highly Uniform Switching. Journal of Nanoscience and Nanotechnology, 2014, 14, 5166-5170.	0.9	3
100	High performance IGZO/TiO2 thin film transistors using Y2O3 buffer layers on polycarbonate substrate. Applied Physics A: Materials Science and Processing, 2013, 112, 817-820.	2.3	15
101	Nano-crystallized titanium oxide resistive memory with uniform switching and long endurance. Applied Physics A: Materials Science and Processing, 2013, 111, 203-207.	2.3	8
102	Fully room-temperature IGZO thin film transistors adopting stacked gate dielectrics on flexible polycarbonate substrate. Solid-State Electronics, 2013, 89, 194-197.	1.4	28
103	Room-temperature flexible thin film transistor with high mobility. Current Applied Physics, 2013, 13, 1459-1462.	2.4	11
104	Evaluation of Temperature Stability of Trilayer Resistive Memories Using Work-Function Tuning. Applied Physics Express, 2013, 6, 041203.	2.4	1
105	Structural stability of thermoelectric diffusion barriers: Experimental results and first principles calculations. Applied Physics Letters, 2013, 103, .	3.3	15
106	$hbox{Ni/GeO}_{x}hbox{/TiO}_{y}hbox{/TaN}$ RRAM on Flexible Substrate With Excellent Resistance Distribution. IEEE Electron Device Letters, 2013, 34, 505-507.	3.9	45
107	A low operating voltage IGZO TFT using LaLuO<inf>3</inf> gate dielectric. , 2013, , .		0
108	GeO<inf>2</inf>/PZT resistive random access memory devices with Ni electrode. , 2013, , .		0

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109	Crystallized Ohmic Contact Effect in AlGaN/GaN High Electron Mobility Transistor. Japanese Journal of Applied Physics, 2013, 52, 081001.	1.5	1
110	Achieving low sub-0.6-nm EOT in gate-first n-MOSFET with TiLaO/CeO2 gate stack. Solid-State Electronics, 2013, 82, 111-114.	1.4	2
111	Gate-first n-MOSFET with a sub-0.6-nm EOT gate stack. Microelectronic Engineering, 2013, 109, 35-38.	2.4	8
112	Flexible InGaZnO thin film transistors using stacked Y₂O₃/TiO₂/Y₂O₃ gate dielectrics grown at room temperature. Physica Status Solidi - Rapid Research Letters, 2013, 7, 285-288.	2.4	17
113	Low Operation Voltage InGaZnO Thin Film Transistors with LaAlO₃Gate Dielectric Incorporation. ECS Journal of Solid State Science and Technology, 2013, 2, N179-N181.	1.8	14
114	A Flexible IGZO Thin-Film Transistor With Stacked ${m TiO}_{2}$-Based Dielectrics Fabricated at Room Temperature. IEEE Electron Device Letters, 2013, 34, 768-770.	3.9	103
115	Current uniformity improvement in flexible resistive memory. , 2013, , .		0
116	Flexible InGaZnO TFTs with stacked GeO<inf>2</inf>/TiO<inf>2</inf> gate dielectrics. , 2013, , .		0
117	Thermoelectric Characteristics of Annealed N-Type BiTe Thin Film. ECS Transactions, 2012, 41, 27-36.	0.5	0
118	Improved current distribution in resistive memory on flexible substrate using nitrogen-rich TaN electrode. Applied Physics Letters, 2012, 101, .	3.3	11
119	Mechanism of GeO₂ resistive switching based on the multi-phonon assisted tunneling between traps. Applied Physics Letters, 2012, 100, 243506.	3.3	63
120	Highly uniform low-power resistive memory using nitrogen-doped tantalum pentoxide. Solid-State Electronics, 2012, 73, 60-63.	1.4	14
121	Ultralow Switching Energy Ni/$hbox{GeO}_{x}$/HfON/TaN RRAM. IEEE Electron Device Letters, 2011, 32, 366-368.	3.9	37
122	Long-Endurance Nanocrystal $hbox{TiO}_{2}$ Resistive Memory Using a TaON Buffer Layer. IEEE Electron Device Letters, 2011, 32, 1749-1751.	3.9	34
123	High-field mobility metal-gate/high-Îº Ge n-MOSFETs with small equivalent-oxide-thickness. Solid-State Electronics, 2011, 55, 64-67.	1.4	6
124	Lowâ€Power Highâ€Performance Nonâ€Volatile Memory on a Flexible Substrate with Excellent Endurance. Advanced Materials, 2011, 23, 902-905.	21.0	130
125	Bipolar switching characteristics of low-power Geo resistive memory. Solid-State Electronics, 2011, 62, 90-93.	1.4	5
126	Unipolar Ni/GeO$_{x}$/PbZr$_{0.5}$Ti$_{0.5}$O$_{3}$/TaN Resistive Switching Memory. Japanese Journal of Applied Physics, 2011, 50, 121801.	1.5	2

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127	The Reliability Study and Device Modeling for p-HEMT Microwave Power Transistors. ECS Transactions, 2011, 41, 175-187.	0.5	0
128	Characteristics of 4H-SiC RF MOSFETs on a Semi-Insualting Substrate. ECS Transactions, 2011, 35, 173-183.	0.5	2
129	Size-Dependent Trapping Effect in Nano-Dot Non-Volatile Memory. ECS Transactions, 2011, 41, 121-132.	0.5	0
130	Unipolar Ni/GeO_x/PbZr_{0.5}Ti_{0.5}O₃/TaN Resistive Switching Memory. Japanese Journal of Applied Physics, 2011, 50, 121801.	1.5	2
131	High-Performance Gate-First Epitaxial Ge n-MOSFETs on Si With $hbox{LaAlO}_{3}$ Gate Dielectrics. IEEE Transactions on Electron Devices, 2010, 57, 3525-3530.	3.0	4
132	Evaluation of the nanoindentation behaviors of SiGe epitaxial layer on Si substrate. Microelectronics Reliability, 2010, 50, 63-69.	1.7	22
133	Higher-Î¤ titanium dioxide incorporating LaAlO3 as dielectrics for MIM capacitors. Solid-State Electronics, 2010, 54, 646-649.	1.4	2
134	A Study on Frequency-Dependent Voltage Nonlinearity of SrTiO[sub 3] rf Capacitor. Electrochemical and Solid-State Letters, 2010, 13, H436.	2.2	7
135	Flow Rate's Influence on Low Temperature Silicon Oxide Deposited by Atmospheric Pressure Plasma Jet for Organic Thin Film Tranisitor Application. ECS Transactions, 2010, 33, 255-264.	0.5	0
136	Lanthanide-Oxides Mixed TiO[sub 2] Dielectrics for High-Î¤ MIM Capacitors. Journal of the Electrochemical Society, 2010, 157, H821.	2.9	3
137	Highly scaled charge-trapping layer of ZrON nonvolatile memory device with good retention. Applied Physics Letters, 2010, 97, .	3.3	15
138	High-Î¤ TiCeO MIM Capacitors with a Dual-Plasma Interface Treatment. Electrochemical and Solid-State Letters, 2010, 13, H112.	2.2	1
139	High Capacitance Density and Thermal Leakage Improvement by Using High-Î¤ Al[sub 2]O[sub 3]-Doped SrTiO[sub 3] MIM Capacitors. Journal of the Electrochemical Society, 2010, 157, H624.	2.9	4
140	High-Performance Metalâ€“Insulatorâ€“Metal Capacitors With $hbox{HfTiO}/hbox{Y}_{2}hbox{O}_{3}$ Stacked Dielectric. IEEE Electron Device Letters, 2010, 31, 875-877.	3.9	21
141	Ultralow-Power Ni/GeO/STO/TaN Resistive Switching Memory. IEEE Electron Device Letters, 2010, 31, 1020-1022.	3.9	18
142	Performance Improvement of Metalâ€“Insulatorâ€“Metal Capacitors Using Postmetallization-Annealed Treatment on the Al[sub 2]O[sub 3]â^•TiO[sub 2]â^•Al[sub 2]O[sub 3] Film. Electrochemical and Solid-State Letters, 2009, 12, H123.	2.2	3
143	Effect of Ta2O5Doping on Electrical Characteristics of SrTiO3Metalâ€“Insulatorâ€“Metal Capacitors. Japanese Journal of Applied Physics, 2009, 48, 081401.	1.5	2
144	Improved Lower Electrode Oxidation of High-k TiCeO Metal-Insulator-Metal Capacitors by Using Dual Plasma Treatment. ECS Transactions, 2009, 16, 323-333.	0.5	0

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145	Low-Threshold-Voltage TaN/LaTiO n-MOSFETs With Small EOT. IEEE Electron Device Letters, 2009, 30, 999-1001.	3.9	12
146	High-Performance Metal-Insulator-Metal Capacitor Using Quality Properties of High-Î¤ TiPrO Dielectric. Journal of the Electrochemical Society, 2009, 156, G23.	2.9	8
147	Low-Threshold-Voltage TaN/Ir/LaTiO p-MOSFETs Incorporating Low-Temperature-Formed Shallow Junctions. IEEE Electron Device Letters, 2009, 30, 681-683.	3.9	4
148	High performance metal/insulator/metal capacitors using HfTiO as dielectric. , 2009, , .		3
149	Improvement of the Performance of TiHfO MIM Capacitors by Using a Dual Plasma Treatment of the Lower Electrode. IEEE Electron Device Letters, 2008, 29, 1105-1107.	3.9	19
150	High Density and Low Leakage Current in $ hbox{TiO}_{2}$ MIM Capacitors Processed at 300 $^{circ} hbox{C}$. IEEE Electron Device Letters, 2008, 29, 845-847.	3.9	62
151	High-Performance MIM Capacitors Using a High-Î¤ TiZrO Dielectric. Journal of the Electrochemical Society, 2008, 155, G295.	2.9	8
152	Low-Voltage Organic Thin-Film Transistor With High-Î¤ LaYOx Gate Insulator. ECS Transactions, 2008, 16, 231-237.	0.5	0
153	Improved Stress Reliability of Analog TiHfO Metalâ€“Insulatorâ€“Metal Capacitors Using High-Work-Function Electrode. Japanese Journal of Applied Physics, 2007, 46, 7300.	1.5	15
154	Use of a High-Work-Function Ni Electrode to Improve the Stress Reliability of Analog $hbox{SrTiO}_{3}$ Metalâ€“Insulatorâ€“Metal Capacitors. IEEE Electron Device Letters, 2007, 28, 694-696.	3.9	36
155	Leakage Current Improvement of Niâ•TiNiOâ•TaN Metal-Insulator-Metal Capacitors using Optimized N[sup +] Plasma Treatment and Oxygen Annealing. Electrochemical and Solid-State Letters, 2007, 10, H287.	2.2	10
156	Thermal Leakage Improvement by Using a High-Work-Function Ni Electrode in High-Î¤ TiHfO Metalâ€“Insulatorâ€“Metal Capacitors. Journal of the Electrochemical Society, 2007, 154, G54.	2.9	26
157	Improved High-Temperature Leakage in High-Density MIM Capacitors by Using a TiLaO Dielectric and an Ir Electrode. IEEE Electron Device Letters, 2007, 28, 1095-1097.	3.9	46
158	High-Temperature Leakage Improvement in Metalâ€“Insulatorâ€“Metal Capacitors by Workâ€“Function Tuning. IEEE Electron Device Letters, 2007, 28, 235-237.	3.9	51